

DATA SHEET

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74AHC2G125; 74AHCT2G125 Bus buffer/line driver; 3-state

Product specification

2004 Jan 13

Bus buffer/line driver; 3-state**74AHC2G125; 74AHCT2G125****FEATURES**

- Symmetrical output impedance
- High noise immunity
- ESD protection:
 - HBM EIA/JESD22-A114-A exceeds 2000 V
 - MM EIA/JESD22-A115-A exceeds 200 V
 - CDM EIA/JESD22-C101 exceeds 1000 V.
- Low power dissipation
- Balanced propagation delays
- SOT505-2 and SOT765-1 package
- Specified from –40 to +85 °C and –40 to +125 °C.

DESCRIPTION

The 74AHC2G/AHCT2G125 is a high-speed Si-gate CMOS device.

The 74AHC2G/AHCT2G125 provides a dual non-inverting buffer/line driver with 3-state output. The 3-state output is controlled by the output enable input ($\overline{\text{nOE}}$). A HIGH at pin $\overline{\text{nOE}}$ causes the output to assume a high-impedance OFF-state.

QUICK REFERENCE DATA

GND = 0 V; $T_{\text{amb}} = 25\text{ °C}$; $t_r = t_f \leq 3.0\text{ ns}$.

SYMBOL	PARAMETER	CONDITIONS	TYPICAL		UNIT
			AHC2G	AHCT2G	
$t_{\text{PHL}}/t_{\text{PLH}}$	propagation delay nA to nY	$C_L = 15\text{ pF}$; $V_{\text{CC}} = 5\text{ V}$	3.4	3.4	ns
C_i	input capacitance		1.5	1.5	pF
C_{PD}	power dissipation capacitance	$C_L = 50\text{ pF}$; $f = 1\text{ MHz}$; notes 1 and 2	9	11	pF

Notes

1. C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

$$P_D = C_{\text{PD}} \times V_{\text{CC}}^2 \times f_i \times N + \sum (C_L \times V_{\text{CC}}^2 \times f_o) \text{ where:}$$

f_i = input frequency in MHz;

f_o = output frequency in MHz;

C_L = output load capacitance in pF;

V_{CC} = supply voltage in Volts;

N = total load switching outputs;

$\sum (C_L \times V_{\text{CC}}^2 \times f_o)$ = sum of outputs.

2. The condition is $V_i = \text{GND to } V_{\text{CC}}$.

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FUNCTION TABLE

See note 1.

INPUT		OUTPUT
$\overline{\text{nOE}}$	nA	nY
L	L	L
L	H	H
H	X	Z

Note

1. H = HIGH voltage level;
L = LOW voltage level;
X = don't care;
Z = high-impedance OFF-state.

ORDERING INFORMATION

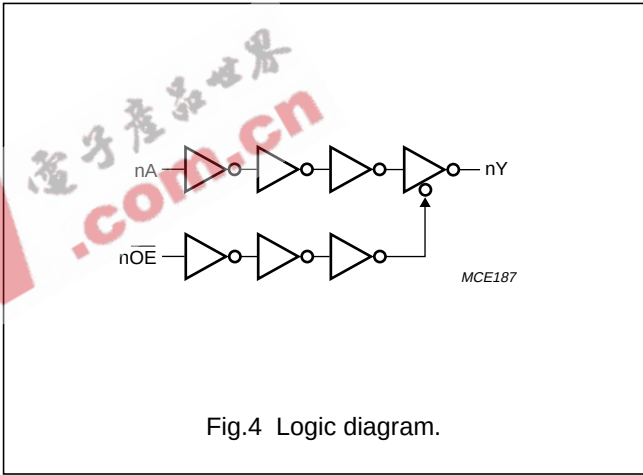
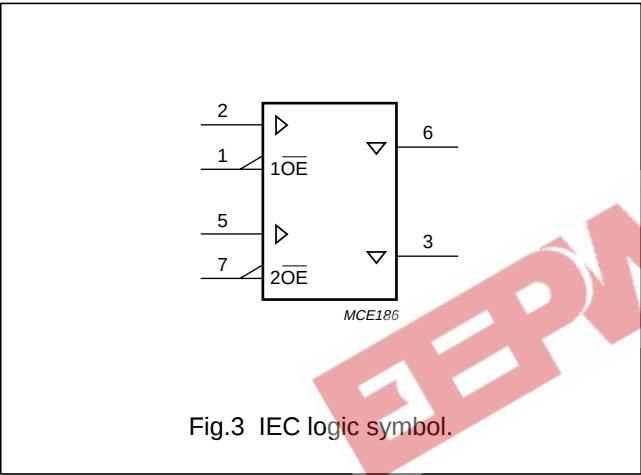
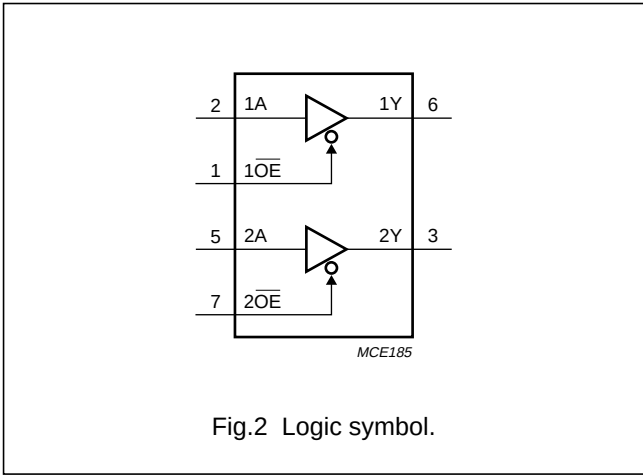
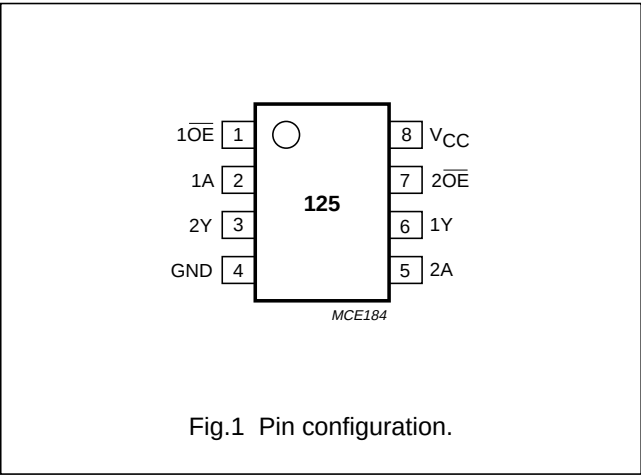
TYPE NUMBER	PACKAGE					
	TEMPERATURE RANGE	PINS	PACKAGE	MATERIAL	CODE	MARKING
74AHC2G125DP	-40 to +125 °C	8	TSSOP8	plastic	SOT505-2	A25
74AHCT2G125DP	-40 to +125 °C	8	TSSOP8	plastic	SOT505-2	C25
74AHC2G125DC	-40 to +125 °C	8	VSSOP8	plastic	SOT765-1	A25
74AHCT2G125DC	-40 to +125 °C	8	VSSOP8	plastic	SOT765-1	C25

PINNING

PIN	SYMBOL	DESCRIPTION
1	1OE	output enable input (active LOW)
2	1A	data input
3	2Y	data output
4	GND	ground (0 V)
5	2A	data input
6	1Y	data output
7	2OE	output enable input (active LOW)
8	V _{CC}	supply voltage

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RECOMMENDED OPERATING CONDITIONS

SYMBOL	PARAMETER	CONDITIONS	74AHC2G125			74AHCT2G125			UNIT
			MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
V_{CC}	supply voltage		2.0	5.0	5.5	4.5	5.0	5.5	V
V_I	input voltage		0	–	5.5	0	–	5.5	V
V_O	output voltage		0	–	V_{CC}	0	–	V_{CC}	V
T_{amb}	operating ambient temperature	see DC and AC characteristics per device	–40	+25	+125	–40	+25	+125	°C
t_r, t_f	input rise and fall times	$V_{CC} = 3.3 \pm 0.3$ V	–	–	100	–	–	–	ns/V
		$V_{CC} = 5 \pm 0.5$ V	–	–	20	–	–	20	ns/V

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134); voltages are referenced to GND (ground = 0 V).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CC}	supply voltage		–0.5	+7.0	V
V_I	input voltage		–0.5	+7.0	V
I_{IK}	input diode current	$V_I < -0.5$ V	–	–20	mA
I_{OK}	output diode current	$V_O < -0.5$ V or $V_O > V_{CC} + 0.5$ V; note 1	–	± 20	mA
I_O	output source or sink current	-0.5 V $< V_O < V_{CC} + 0.5$ V	–	± 25	mA
I_{CC}, I_{GND}	V_{CC} or GND current		–	± 75	mA
T_{stg}	storage temperature		–65	+150	°C
P_{tot}	power dissipation	$T_{amb} = -40$ to $+125$ °C	–	250	mW

Note

1. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

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DC CHARACTERISTICS

Type 74AHC2G125

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

SYMBOL	PARAMETER	CONDITIONS		MIN.	TYP.	MAX.	UNIT
		OTHER	V _{CC} (V)				
T _{amb} = 25 °C							
V _{IH}	HIGH-level input voltage		2.0	1.5	–	–	V
			3.0	2.1	–	–	V
			5.5	3.85	–	–	V
V _{IL}	LOW-level input voltage		2.0	–	–	0.5	V
			3.0	–	–	0.9	V
			5.5	–	–	1.65	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}					
		I _O = –50 μA	2.0	1.9	2.0	–	V
		I _O = –50 μA	3.0	2.9	3.0	–	V
		I _O = –50 μA	4.5	4.4	4.5	–	V
		I _O = –4.0 mA	3.0	2.58	–	–	V
		I _O = –8.0 mA	4.5	3.94	–	–	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}					
		I _O = 50 μA	2.0	–	0	0.1	V
		I _O = 50 μA	3.0	–	0	0.1	V
		I _O = 50 μA	4.5	–	0	0.1	V
		I _O = 4.0 mA	3.0	–	–	0.36	V
		I _O = 8.0 mA	4.5	–	–	0.36	V
I _{OZ}	3-state output OFF-state current	V _I = V _{CC} or GND	5.5	–	–	0.25	μA
I _{LI}	input leakage current	V _I = V _{CC} or GND	5.5	–	–	0.1	μA
I _{CC}	quiescent supply current	V _I = V _{CC} or GND; I _O = 0	5.5	–	–	1.0	μA
C _I	input capacitance		–	–	1.5	10	pF

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SYMBOL	PARAMETER	CONDITIONS		MIN.	TYP.	MAX.	UNIT		
		OTHER	V _{CC} (V)						
T _{amb} = −40 to +85 °C									
V _{IH}	HIGH-level input voltage		2.0	1.5	–	–	V		
			3.0	2.1	–	–	V		
			5.5	3.85	–	–	V		
V _{IL}	LOW-level input voltage		2.0	–	–	0.5	V		
			3.0	–	–	0.9	V		
			5.5	–	–	1.65	V		
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}							
		I _O = −50 μA	2.0	1.9	–	–	V		
		I _O = −50 μA	3.0	2.9	–	–	V		
		I _O = −50 μA	4.5	4.4	–	–	V		
		I _O = −4.0 mA	3.0	2.48	–	–	V		
V _{OL}	LOW-level output voltage	I _O = −8.0 mA	4.5	3.8	–	–	V		
		V _I = V _{IH} or V _{IL}							
		I _O = 50 μA	2.0	–	–	0.1	V		
		I _O = 50 μA	3.0	–	–	0.1	V		
		I _O = 50 μA	4.5	–	–	0.1	V		
I _{OZ}	3-state output OFF-state current	I _O = 4.0 mA	3.0	–	–	0.44	V		
		I _O = 8.0 mA	4.5	–	–	0.44	V		
		V _I = V _{CC} or GND	5.5	–	–	2.5	μA		
		I _I	input leakage current	V _I = V _{CC} or GND	5.5	–	–	1.0	μA
		I _{CC}	quiescent supply current	V _I = V _{CC} or GND; I _O = 0	5.5	–	–	10	μA
C _I	input capacitance		–	–	–	10	pF		

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SYMBOL	PARAMETER	CONDITIONS		MIN.	TYP.	MAX.	UNIT
		OTHER	V _{CC} (V)				
T _{amb} = −40 to +125 °C							
V _{IH}	HIGH-level input voltage		2.0	1.5	–	–	V
			3.0	2.1	–	–	V
			5.5	3.85	–	–	V
V _{IL}	LOW-level input voltage		2.0	–	–	0.5	V
			3.0	–	–	0.9	V
			5.5	–	–	1.65	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}					
		I _O = −50 μA	2.0	1.9	–	–	V
		I _O = −50 μA	3.0	2.9	–	–	V
		I _O = −50 μA	4.5	4.4	–	–	V
		I _O = −4.0 mA	3.0	2.40	–	–	V
		I _O = −8.0 mA	4.5	3.70	–	–	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}					
		I _O = 50 μA	2.0	–	–	0.1	V
		I _O = 50 μA	3.0	–	–	0.1	V
		I _O = 50 μA	4.5	–	–	0.1	V
		I _O = 4.0 mA	3.0	–	–	0.55	V
		I _O = 8.0 mA	4.5	–	–	0.55	V
I _{OZ}	3-state output OFF-state current	V _I = V _{CC} or GND	5.5	–	–	10	μA
I _{LI}	input leakage current	V _I = V _{CC} or GND	5.5	–	–	2.0	μA
I _{CC}	quiescent supply current	V _I = V _{CC} or GND; I _O = 0	5.5	–	–	40	μA
C _I	input capacitance		–	–	–	10	pF

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Type 74AHCT2G125

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

SYMBOL	PARAMETER	CONDITIONS		MIN.	TYP.	MAX.	UNIT
		OTHER	V _{CC} (V)				
T _{amb} = 25 °C							
V _{IH}	HIGH-level input voltage		4.5 to 5.5	2.0	–	–	V
V _{IL}	LOW-level input voltage		4.5 to 5.5	–	–	0.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}					
		I _O = –50 μA	4.5	4.4	4.5	–	V
		I _O = –8.0 mA	4.5	3.94	–	–	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}					
		I _O = 50 μA	4.5	–	0	0.1	V
		I _O = 8.0 mA	4.5	–	–	0.36	V
I _{OZ}	3-state output OFF-state current	V _I = V _{CC} or GND	5.5	–	–	0.25	μA
I _{LI}	input leakage current	V _I = V _{IH} or V _{IL}	5.5	–	–	0.1	μA
I _{CC}	quiescent supply current	V _I = V _{CC} or GND; I _O = 0	5.5	–	–	1.0	μA
ΔI _{CC}	additional quiescent supply current per input pin	V _I = 3.4 V; other inputs at V _{CC} or GND; I _O = 0	5.5	–	–	1.35	mA
C _I	input capacitance			–	1.5	10	pF
T _{amb} = –40 to +85 °C							
V _{IH}	HIGH-level input voltage		4.5 to 5.5	2.0	–	–	V
V _{IL}	LOW-level input voltage		4.5 to 5.5	–	–	0.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}					
		I _O = –50 μA	4.5	4.4	–	–	V
		I _O = –8.0 mA	4.5	3.8	–	–	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}					
		I _O = 50 μA	4.5	–	–	0.1	V
		I _O = 8.0 mA	4.5	–	–	0.44	V
I _{OZ}	3-state output OFF-state current	V _I = V _{CC} or GND	5.5	–	–	2.5	μA
I _{LI}	input leakage current	V _I = V _{IH} or V _{IL}	5.5	–	–	1.0	μA
I _{CC}	quiescent supply current	V _I = V _{CC} or GND; I _O = 0	5.5	–	–	10	μA
ΔI _{CC}	additional quiescent supply current per input pin	V _I = 3.4 V; other inputs at V _{CC} or GND; I _O = 0	5.5	–	–	1.5	mA
C _I	input capacitance		–	–	–	10	pF

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SYMBOL	PARAMETER	CONDITIONS		MIN.	TYP.	MAX.	UNIT
		OTHER	V _{CC} (V)				
T _{amb} = -40 to +125 °C							
V _{IH}	HIGH-level input voltage		4.5 to 5.5	2.0	—	—	V
V _{IL}	LOW-level input voltage		4.5 to 5.5	—	—	0.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}					
		I _O = -50 μA	4.5	4.4	—	—	V
		I _O = -8.0 mA	4.5	3.70	—	—	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}					
		I _O = 50 μA	4.5	—	—	0.1	V
		I _O = 8.0 mA	4.5	—	—	0.55	V
I _{OZ}	3-state output OFF-state current	V _I = V _{CC} or GND	5.5	—	—	10	μA
I _{LI}	input leakage current	V _I = V _{IH} or V _{IL}	5.5	—	—	2.0	μA
I _{CC}	quiescent supply current	V _I = V _{CC} or GND; I _O = 0	5.5	—	—	40	μA
ΔI _{CC}	additional quiescent supply current per input pin	V _I = 3.4 V; other inputs at V _{CC} or GND; I _O = 0	5.5	—	—	1.5	mA
C _I	input capacitance		—	—	—	10	pF

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AC CHARACTERISTICS

Type 74AHC2G125

GND = 0 V; $t_r = t_f \leq 3.0$ ns.

SYMBOL	PARAMETER	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
		WAVEFORMS	C _L (pF)				
T _{amb} = 25 °C							
V _{CC} = 3.0 to 3.6 V; note 1							
t _{PHL} /t _{PLH}	propagation delay nA to nY	see Figs 5 and 7	15	–	4.7	8.0	ns
t _{PZH} /t _{PZL}	propagation delay n $\overline{OE}$ to nY	see Figs 6 and 7	15	–	5.0	8.0	ns
t _{PHZ} /t _{PLZ}	propagation delay n $\overline{OE}$ to nY	see Figs 6 and 7	15	–	6.0	9.7	ns
t _{PHL} /t _{PLH}	propagation delay nA to nY	see Figs 5 and 7	50	–	6.6	11.5	ns
t _{PZH} /t _{PZL}	propagation delay n $\overline{OE}$ to nY	see Figs 6 and 7	50	–	6.9	11.5	ns
t _{PHZ} /t _{PLZ}	propagation delay n $\overline{OE}$ to nY	see Figs 6 and 7	50	–	8.3	13.2	ns
V _{CC} = 4.5 to 5.5 V; note 2							
t _{PHL} /t _{PLH}	propagation delay nA to nY	see Figs 5 and 7	15	–	3.4	5.5	ns
t _{PZH} /t _{PZL}	propagation delay n $\overline{OE}$ to nY	see Figs 6 and 7	15	–	3.6	5.1	ns
t _{PHZ} /t _{PLZ}	propagation delay n $\overline{OE}$ to nY	see Figs 6 and 7	15	–	4.1	6.8	ns
t _{PHL} /t _{PLH}	propagation delay nA to nY	see Figs 5 and 7	50	–	4.8	7.5	ns
t _{PZH} /t _{PZL}	propagation delay n $\overline{OE}$ to nY	see Figs 6 and 7	50	–	4.9	7.5	ns
t _{PHZ} /t _{PLZ}	propagation delay n $\overline{OE}$ to nY	see Figs 6 and 7	50	–	5.7	8.8	ns
T _{amb} = –40 to +85 °C							
V _{CC} = 3.0 to 3.6 V; note 1							
t _{PHL} /t _{PLH}	propagation delay nA to nY	see Figs 5 and 7	15	1.0	–	9.5	ns
t _{PZH} /t _{PZL}	propagation delay n $\overline{OE}$ to nY	see Figs 6 and 7	15	1.0	–	9.5	ns
t _{PHZ} /t _{PLZ}	propagation delay n $\overline{OE}$ to nY	see Figs 6 and 7	15	1.0	–	11.5	ns
t _{PHL} /t _{PLH}	propagation delay nA to nY	see Figs 5 and 7	50	1.0	–	13.0	ns
t _{PZH} /t _{PZL}	propagation delay n $\overline{OE}$ to nY	see Figs 6 and 7	50	1.0	–	13.0	ns
t _{PHZ} /t _{PLZ}	propagation delay n $\overline{OE}$ to nY	see Figs 6 and 7	50	1.0	–	15.0	ns
V _{CC} = 4.5 to 5.5 V; note 2							
t _{PHL} /t _{PLH}	propagation delay nA to nY	see Figs 5 and 7	15	1.0	–	6.5	ns
t _{PZH} /t _{PZL}	propagation delay n $\overline{OE}$ to nY	see Figs 6 and 7	15	1.0	–	6.0	ns
t _{PHZ} /t _{PLZ}	propagation delay n $\overline{OE}$ to nY	see Figs 6 and 7	15	1.0	–	8.0	ns
t _{PHL} /t _{PLH}	propagation delay nA to nY	see Figs 5 and 7	50	1.0	–	8.5	ns
t _{PZH} /t _{PZL}	propagation delay n $\overline{OE}$ to nY	see Figs 6 and 7	50	1.0	–	8.5	ns
t _{PHZ} /t _{PLZ}	propagation delay n $\overline{OE}$ to nY	see Figs 6 and 7	50	1.0	–	10.0	ns

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SYMBOL	PARAMETER	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
		WAVEFORMS	C _L (pF)				
T _{amb} = −40 to +125 °C							
V _{CC} = 3.0 to 3.6 V; note 1							
t _{PHL} /t _{PLH}	propagation delay nA to nY	see Figs 5 and 7	15	1.0	–	11.5	ns
t _{PZH} /t _{PZL}	propagation delay n $\overline{\text{OE}}$ to nY	see Figs 6 and 7	15	1.0	–	11.5	ns
t _{PHZ} /t _{PLZ}	propagation delay n $\overline{\text{OE}}$ to nY	see Figs 6 and 7	15	1.0	–	12.5	ns
t _{PHL} /t _{PLH}	propagation delay nA to nY	see Figs 5 and 7	50	1.0	–	14.5	ns
t _{PZH} /t _{PZL}	propagation delay n $\overline{\text{OE}}$ to nY	see Figs 6 and 7	50	1.0	–	14.5	ns
t _{PHZ} /t _{PLZ}	propagation delay n $\overline{\text{OE}}$ to nY	see Figs 6 and 7	50	1.0	–	16.5	ns
V _{CC} = 4.5 to 5.5 V; note 2							
t _{PHL} /t _{PLH}	propagation delay nA to nY	see Figs 5 and 7	15	1.0	–	7.0	ns
t _{PZH} /t _{PZL}	propagation delay n $\overline{\text{OE}}$ to nY	see Figs 6 and 7	15	1.0	–	6.5	ns
t _{PHZ} /t _{PLZ}	propagation delay n $\overline{\text{OE}}$ to nY	see Figs 6 and 7	15	1.0	–	8.5	ns
t _{PHL} /t _{PLH}	propagation delay nA to nY	see Figs 5 and 7	50	1.0	–	9.5	ns
t _{PZH} /t _{PZL}	propagation delay n $\overline{\text{OE}}$ to nY	see Figs 6 and 7	50	1.0	–	9.5	ns
t _{PHZ} /t _{PLZ}	propagation delay n $\overline{\text{OE}}$ to nY	see Figs 6 and 7	50	1.0	–	11.0	ns

Notes

1. All typical values are measured at V_{CC} = 3.3 V.
2. All typical values are measured at V_{CC} = 5.0 V.

Type 74AHCT2G125GND = 0 V; t_r = t_f ≤ 3.0 ns.

SYMBOL	PARAMETER	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
		WAVEFORMS	C _L (pF)				
T _{amb} = 25 °C							
V _{CC} = 4.5 to 5.5 V; note 1							
t _{PHL} /t _{PLH}	propagation delay nA to nY	see Figs 5 and 7	15	–	3.4	5.5	ns
t _{PZH} /t _{PZL}	propagation delay n $\overline{\text{OE}}$ to nY	see Figs 6 and 7	15	–	3.9	5.1	ns
t _{PHZ} /t _{PLZ}	propagation delay n $\overline{\text{OE}}$ to nY	see Figs 6 and 7	15	–	4.5	6.8	ns
t _{PHL} /t _{PLH}	propagation delay nA to nY	see Figs 5 and 7	50	–	4.8	7.5	ns
t _{PZH} /t _{PZL}	propagation delay n $\overline{\text{OE}}$ to nY	see Figs 6 and 7	50	–	5.1	7.5	ns
t _{PHZ} /t _{PLZ}	propagation delay n $\overline{\text{OE}}$ to nY	see Figs 6 and 7	50	–	6.1	8.8	ns
T _{amb} = –40 to +85 °C							
V _{CC} = 4.5 to 5.5 V							
t _{PHL} /t _{PLH}	propagation delay nA to nY	see Figs 5 and 7	15	1.0	–	6.5	ns
t _{PZH} /t _{PZL}	propagation delay n $\overline{\text{OE}}$ to nY	see Figs 6 and 7	15	1.0	–	6.0	ns
t _{PHZ} /t _{PLZ}	propagation delay n $\overline{\text{OE}}$ to nY	see Figs 6 and 7	15	1.0	–	8.0	ns
t _{PHL} /t _{PLH}	propagation delay nA to nY	see Figs 5 and 7	50	1.0	–	8.5	ns

Bus buffer/line driver; 3-state

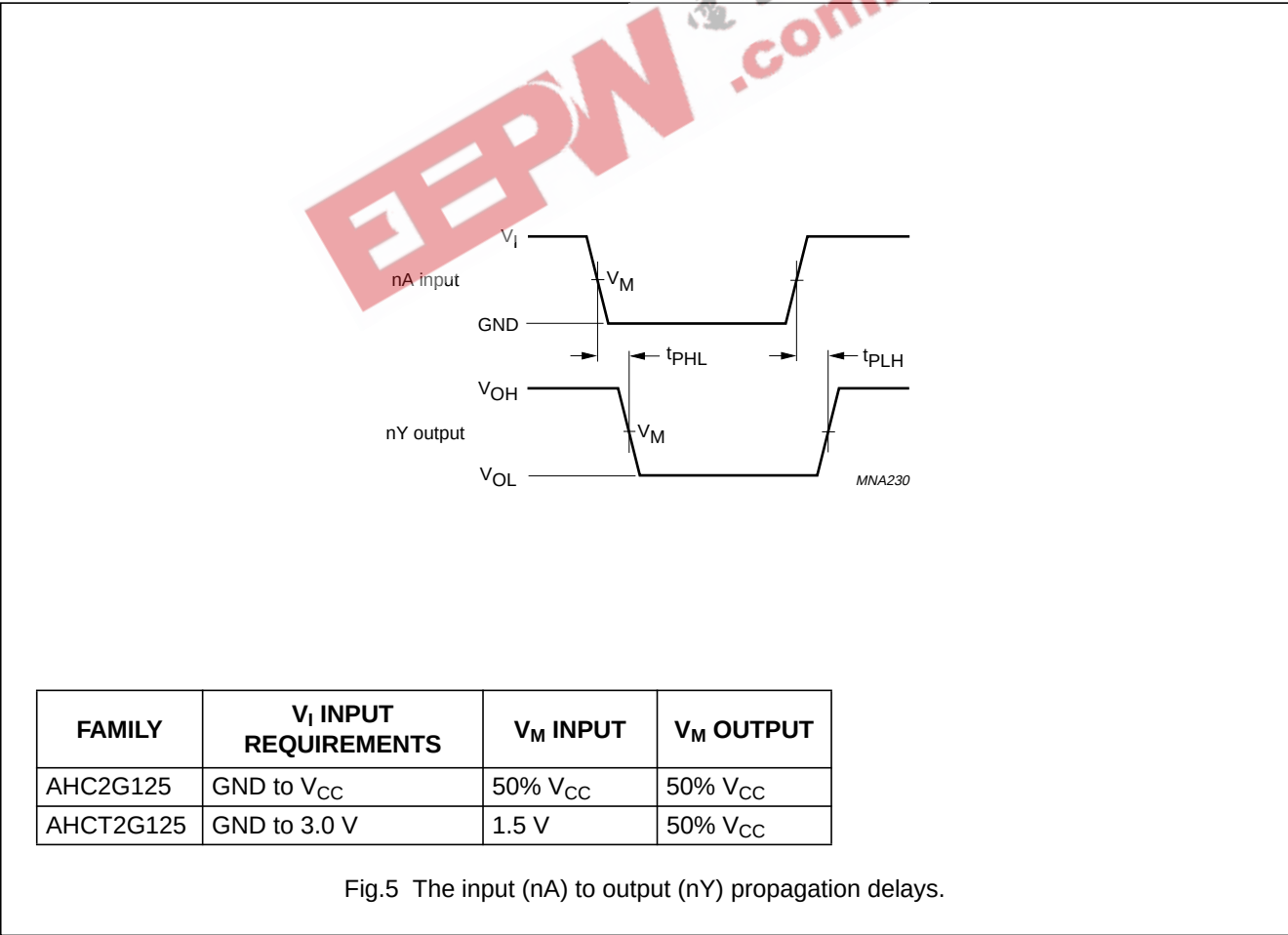
74AHC2G125; 74AHCT2G125

SYMBOL	PARAMETER	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
		WAVEFORMS	C _L (pF)				
t _{PZH} /t _{PZL}	propagation delay n $\overline{\text{OE}}$ to nY	see Figs 6 and 7	50	1.0	–	8.5	ns
t _{PHZ} /t _{PLZ}	propagation delay n $\overline{\text{OE}}$ to nY	see Figs 6 and 7	50	1.0	–	10.0	ns
T _{amb} = –40 to +125 °C							
V _{CC} = 4.5 to 5.5 V							
t _{PHL} /t _{PLH}	propagation delay nA to nY	see Figs 5 and 7	15	1.0	–	6.5	ns
t _{PZH} /t _{PZL}	propagation delay n $\overline{\text{OE}}$ to nY	see Figs 6 and 7	15	1.0	–	6.0	ns
t _{PHZ} /t _{PLZ}	propagation delay n $\overline{\text{OE}}$ to nY	see Figs 6 and 7	15	1.0	–	8.0	ns
t _{PHL} /t _{PLH}	propagation delay nA to nY	see Figs 5 and 7	50	1.0	–	8.5	ns
t _{PZH} /t _{PZL}	propagation delay n $\overline{\text{OE}}$ to nY	see Figs 6 and 7	50	1.0	–	8.5	ns
t _{PHZ} /t _{PLZ}	propagation delay n $\overline{\text{OE}}$ to nY	see Figs 6 and 7	50	1.0	–	10.0	ns

Note

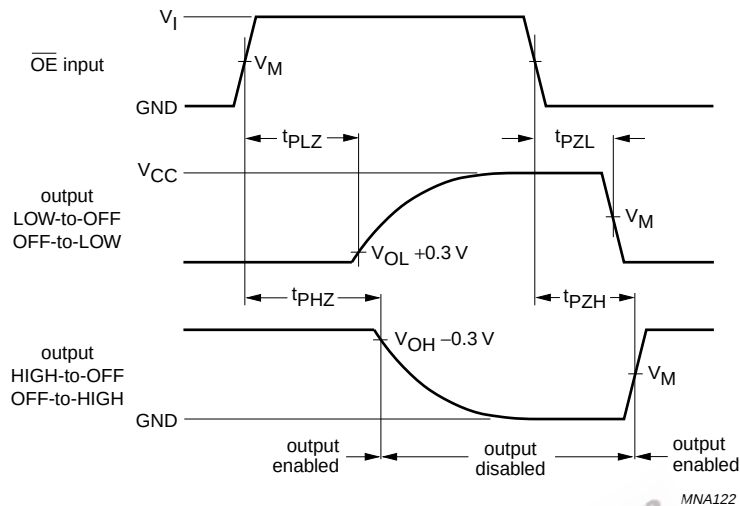
1. All typical values are measured at V_{CC} = 5.0 V.

AC WAVEFORMS



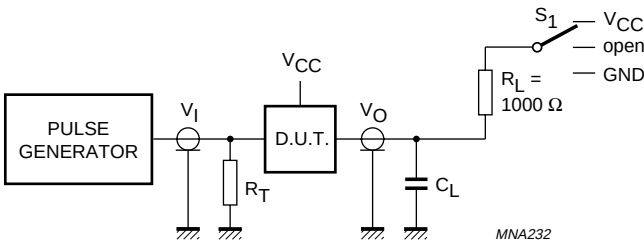
Bus buffer/line driver; 3-state

74AHC2G125; 74AHCT2G125



FAMILY	V _I INPUT REQUIREMENTS	V _M INPUT	V _M OUTPUT
AHC2G125	GND to V _{CC}	50% V _{CC}	50% V _{CC}
AHCT2G125	GND to 3.0 V	1.5 V	50% V _{CC}

Fig.6 The 3-state enable and disable times.



TEST	S ₁
t _{PLH} /t _{PHL}	open
t _{PLZ} /t _{PZL}	V _{CC}
t _{PHZ} /t _{PZH}	GND

Definitions for test circuit:
R_L = load resistance.
C_L = load capacitance including jig and probe capacitance (see Chapter “AC characteristics” for the value).
R_T = termination resistance should be equal to the output impedance Z_o of the pulse generator.

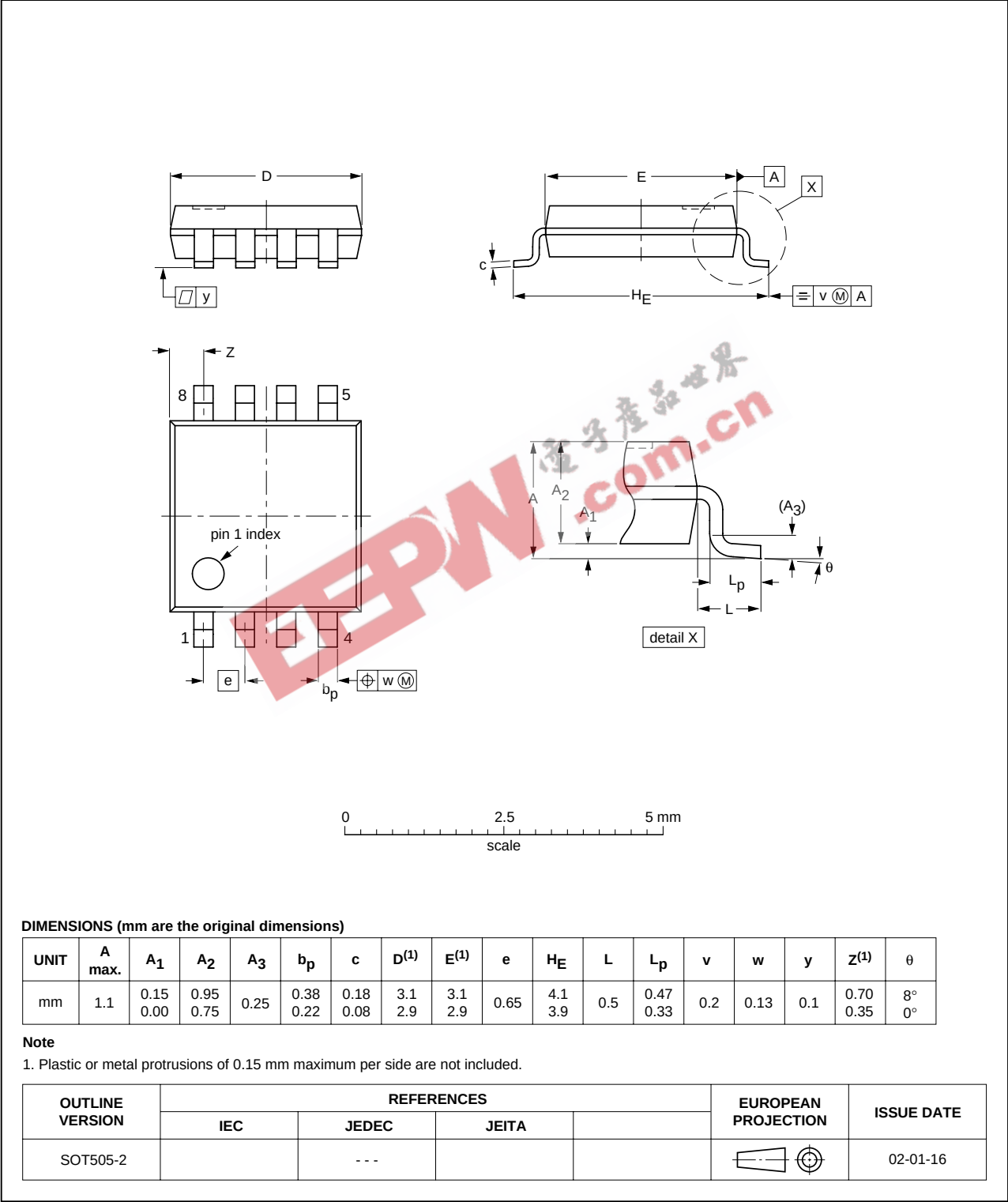
Fig.7 Load circuitry for switching times.

Bus buffer/line driver; 3-state

74AHC2G125; 74AHCT2G125

PACKAGE OUTLINES

TSSOP8: plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm SOT505-2

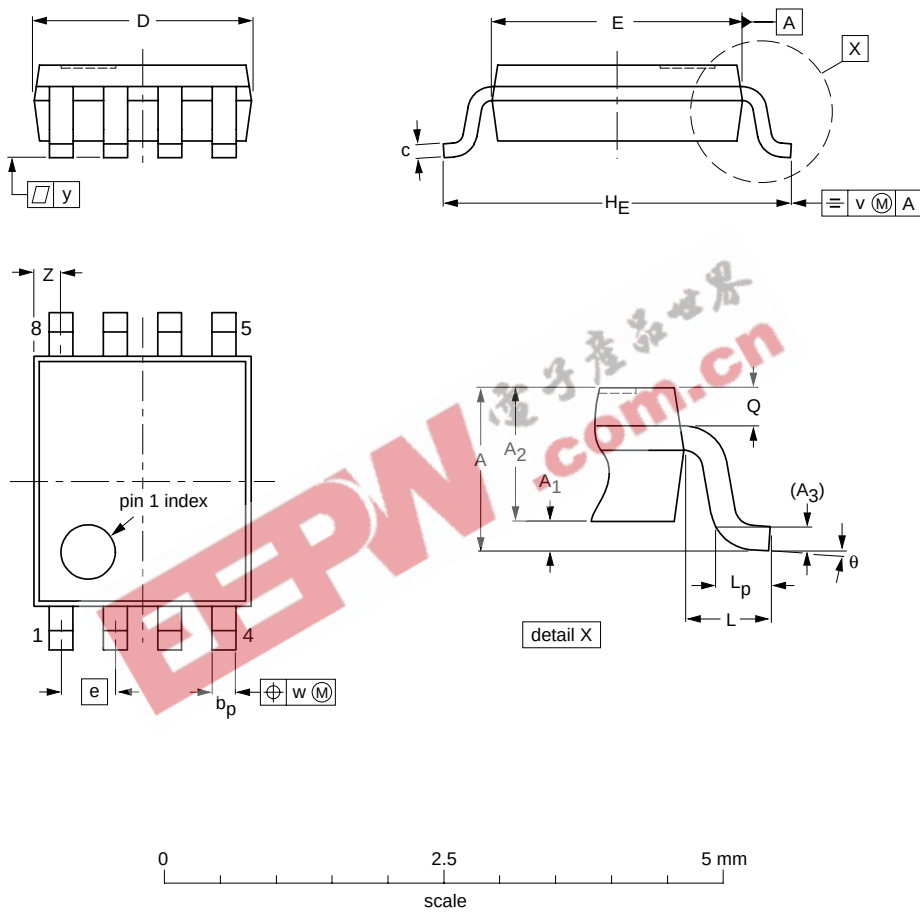


Bus buffer/line driver; 3-state

74AHC2G125; 74AHCT2G125

VSSOP8: plastic very thin shrink small outline package; 8 leads; body width 2.3 mm

SOT765-1



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A ₁	A ₂	A ₃	b _p	c	D ⁽¹⁾	E ⁽²⁾	e	H _E	L	L _p	Q	v	w	y	z ⁽¹⁾	θ
mm	1	0.15 0.00	0.85 0.60	0.12	0.27 0.17	0.23 0.08	2.1 1.9	2.4 2.2	0.5	3.2 3.0	0.4	0.40 0.15	0.21 0.19	0.2	0.13	0.1	0.4 0.1	8° 0°

Notes

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
2. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT765-1		MO-187				02-06-07

Bus buffer/line driver; 3-state

74AHC2G125; 74AHCT2G125

DATA SHEET STATUS

LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾⁽³⁾	DEFINITION
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